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NTE2662

Silicon NPN Transistor

High Frequency, Low Noise RF

Description:

The NTE2662 is a silicon NPN type transistor in a miniature surface mount package designed for oscillator applications up to 3GHz. This device features low voltage operation, low phase noise, and high immunity to pushing effects.

Features:

- New Miniature Surface Mount Package
 - Small Transistor Footprint
 - 1.0mm x 0.5mm x 0.5mm
 - Low Profile / 0.50mm Package Height
 - Flat Lead Style for Better RF Performance
- Ideal for $\leq 3\text{GHz}$ Oscillators
- Low Phase Noise
- Low Pushing Factor

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$, Note 1 unless otherwise specified)

Collector-to-Base Voltage, V_{CBO}	9V
Collector-to-Emitter Voltage, V_{CEO}	5.5V
Emitter-to-Base Voltage, V_{EBO}	1.5V
Collector Current, I_C	100mA
Total Power Dissipation (Note 2), P_T	140mW
Operating Junction Temperature, T_J	$+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-65° to $+150^\circ\text{C}$

Note 1. Operation in excess of any one of these parameters may result in permanent damage.

Note 2. With device mounted on $1.8\text{cm}^2 \times 1.0\text{mm}$ glass epoxy board.

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Gain Bandwidth	f_T	$V_{CE} = 1\text{V}, f = 2\text{GHz}$	$I_C = 5\text{mA}$	3.0	4.5	–	GHz
			$I_C = 15\text{mA}$	5.0	6.5	–	GHz
Insertion Power Gain	$ S_{21E} $	$V_{CE} = 1\text{V}, f = 2\text{GHz},$ Note 3	$I_C = 5\text{mA}$	3.0	4.0	–	dB
			$I_C = 15\text{mA}$	4.5	5.5	–	dB

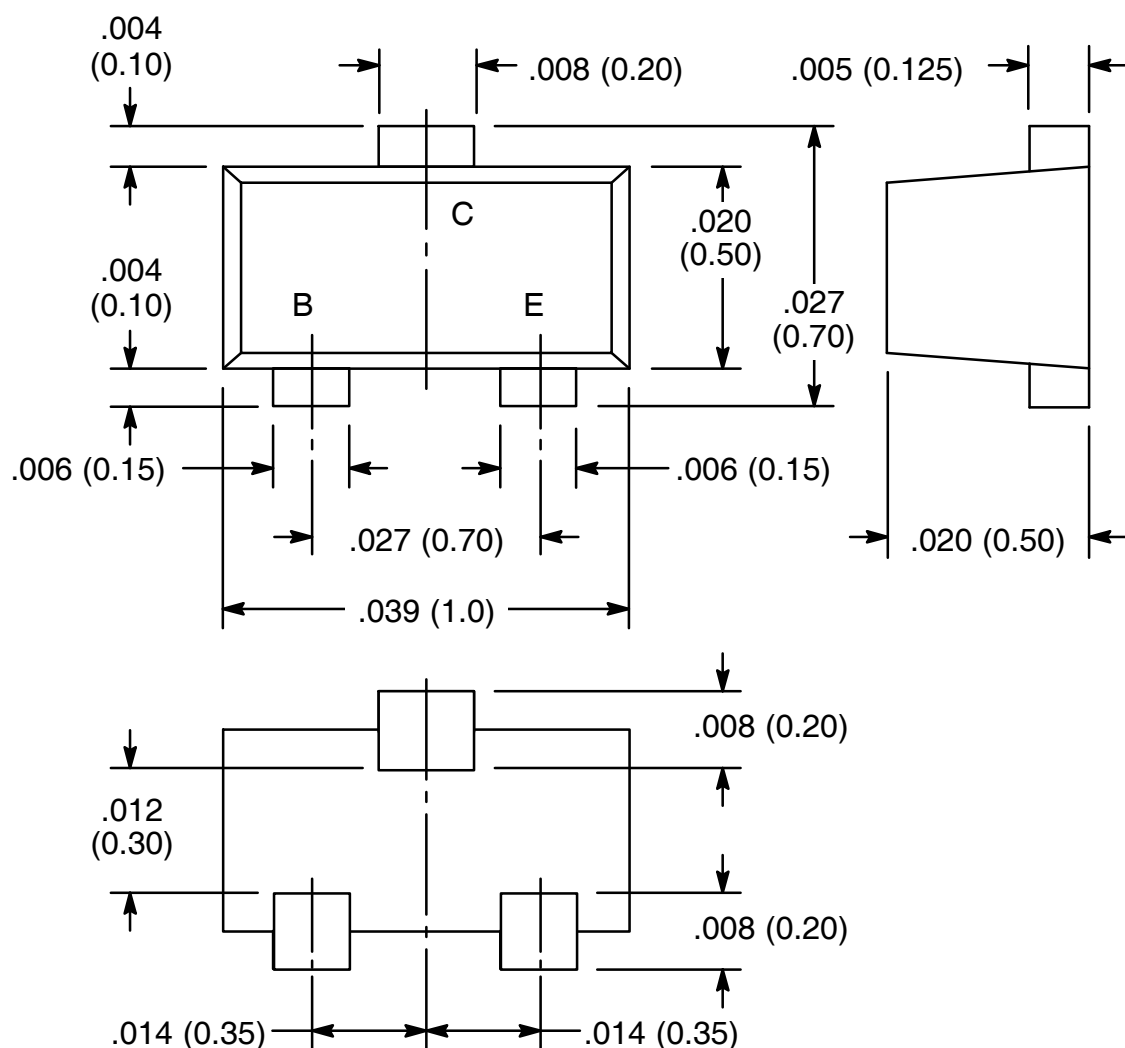
Note 3. Pulsed measurement, Pulse Width $\leq 350\mu\text{s}$, Duty Cycle $\leq 2\%$.

Electrical Characteristics (Cont'd): ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Noise Figure	NF	$V_{CE} = 1\text{V}$, $I_C = 10\text{mA}$, $f = 2\text{GHz}$	–	1.9	2.5	dB
Reverse Transfer Capacitance	C_{RE}	$V_{CB} = 0.5\text{V}$, $I_E = 0\text{mA}$, $f = \text{MHz}$, Note 4	–	0.6	0.8	pF
Collector Cutoff Current	I_{CBO}	$V_{CB} = 5\text{V}$, $I_E = 0$	–	–	600	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 1$, $I_C = 0$	–	–	600	nA
DC Current Gain	h_{FE}	$V_{CE} = 1\text{V}$, $I_C = 5\text{mA}$, Note 3	100	120	145	

Note 3. Pulsed measurement, Pulse Width $\leq 350\mu\text{s}$, Duty Cycle $\leq 2\%$.

Note 4. Collector-to-Base capacitance when the emitter is grounded.



(Bottom View)